

## CLAIMS:

1. A semiconductor component comprising a semiconductor chip 2 made of a doped silicon substrate, which chip is doped into a semiconductor device and structured, and comprises an inner connection metallization 7 in a contact window, and said inner connection metallization of said semiconductor chip is connected to the  
5 respective outer connection metallization by a wire bond connection 9, characterized in that the inner connection metallization comprises a reinforcing system 8 having an open grid structure on the doped silicon substrate.
2. A semiconductor component as claimed in claim 1, characterized in that  
10 the reinforcing system having an open grid structure is formed from an insulation coating.
3. A semiconductor component as claimed in claim 1, characterized in that the grid structure is formed so as to be an open groove structure.  
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4. A semiconductor component as claimed in claim 1, characterized in that the grid structure may be formed so as to be an open tube structure.
5. A semiconductor component as claimed in claim 1, characterized in that  
20 the area of the grid structure of thermal oxide constitutes >50% of the area of the contact window.